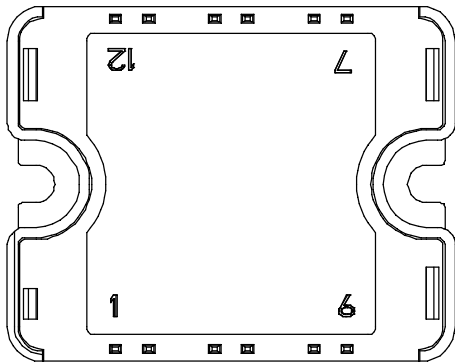
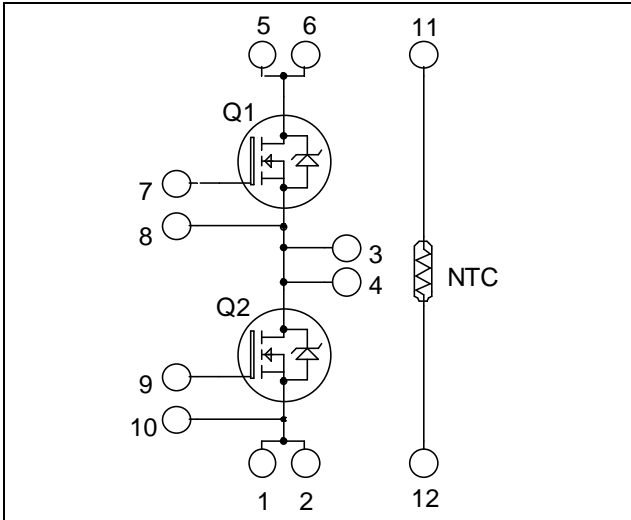


## Phase leg MOSFET Power Module

$V_{DSS} = 500V$   
 $R_{DSon} = 150m\Omega \text{ typ @ } T_j = 25^\circ C$   
 $I_D = 25A \text{ @ } T_c = 25^\circ C$



Pins 1/2 ; 3/4 ; 5/6 must be shorted together

### Application

- Welding converters
- Switched Mode Power Supplies
- Uninterruptible Power Supplies
- Motor control

### Features

- Power MOS 8™ Ultrafast FREDFETs
  - Low  $R_{DSon}$
  - Low input and Miller capacitance
  - Low gate charge
  - Ultrafast intrinsic reverse diode
  - Avalanche energy rated
  - Very rugged
- Very low stray inductance
  - Symmetrical design
- Internal thermistor for temperature monitoring
- High level of integration

### Benefits

- Outstanding performance at high frequency operation
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Solderable terminals both for power and signal for easy PCB mounting
- Low profile
- RoHS Compliant

### Absolute maximum ratings

Symbol	Parameter	Max ratings	Unit
$V_{DSS}$	Drain - Source Breakdown Voltage	500	V
$I_D$	Continuous Drain Current	$T_c = 25^\circ C$	25
		$T_c = 80^\circ C$	19
$I_{DM}$	Pulsed Drain current	135	
$V_{GS}$	Gate - Source Voltage	$\pm 30$	V
$R_{DSon}$	Drain - Source ON Resistance	180	$m\Omega$
$P_D$	Maximum Power Dissipation	$T_c = 25^\circ C$	208
$I_{AR}$	Avalanche current (repetitive and non repetitive)	21	A

**CAUTION:** These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed. See application note APT0502 on [www.microsemi.com](http://www.microsemi.com)

All ratings @  $T_j = 25^\circ\text{C}$  unless otherwise specified

**Electrical Characteristics**

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit	
$I_{DSS}$	Zero Gate Voltage Drain Current	$V_{DS} = 500\text{V}$ $V_{GS} = 0\text{V}$	$T_j = 25^\circ\text{C}$			250	$\mu\text{A}$
			$T_j = 125^\circ\text{C}$			1000	
$R_{DS(on)}$	Drain – Source on Resistance	$V_{GS} = 10\text{V}, I_D = 21\text{A}$		150	180	$\text{m}\Omega$	
$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS} = V_{DS}, I_D = 1\text{mA}$	3	4	5	V	
$I_{GSS}$	Gate – Source Leakage Current	$V_{GS} = \pm 30\text{V}$			$\pm 100$	nA	

**Dynamic Characteristics**

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
$C_{iss}$	Input Capacitance	$V_{GS} = 0\text{V}$ $V_{DS} = 25\text{V}$ $f = 1\text{MHz}$		5448		$\text{pF}$
$C_{oss}$	Output Capacitance			735		
$C_{rss}$	Reverse Transfer Capacitance			72		
$Q_g$	Total gate Charge	$V_{GS} = 10\text{V}$ $V_{Bus} = 250\text{V}$ $I_D = 21\text{A}$		170		nC
$Q_{gs}$	Gate – Source Charge			38		
$Q_{gd}$	Gate – Drain Charge			80		
$T_{d(on)}$	Turn-on Delay Time	<b>Resistive switching @ <math>25^\circ\text{C}</math></b> $V_{GS} = 15\text{V}$ $V_{Bus} = 333\text{V}$ $I_D = 21\text{A}$ $R_G = 4.7\Omega$		29		ns
$T_r$	Rise Time			35		
$T_{d(off)}$	Turn-off Delay Time			80		
$T_f$	Fall Time			26		

**Source - Drain diode ratings and characteristics**

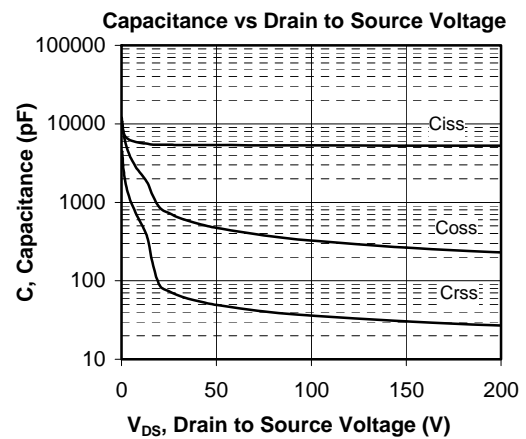
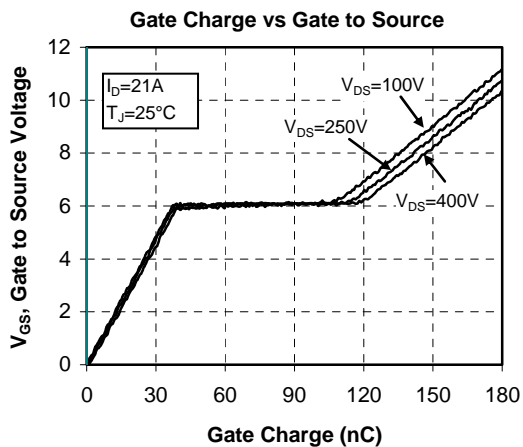
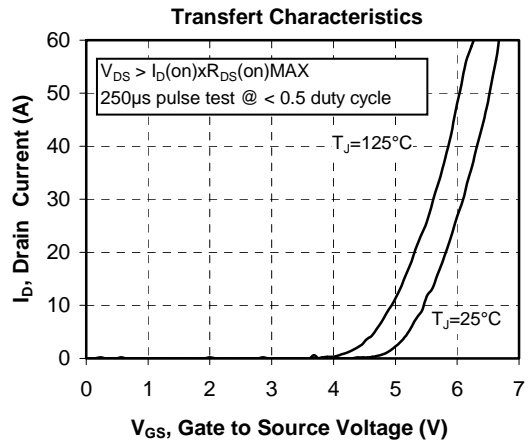
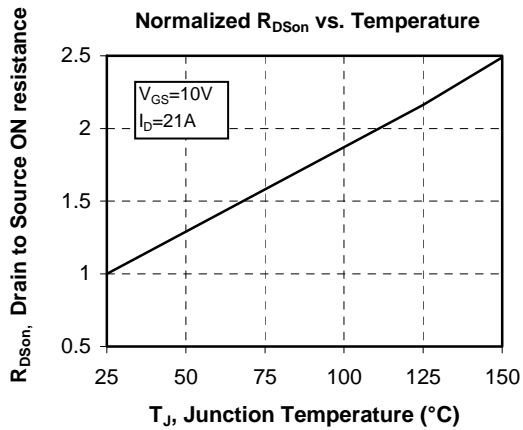
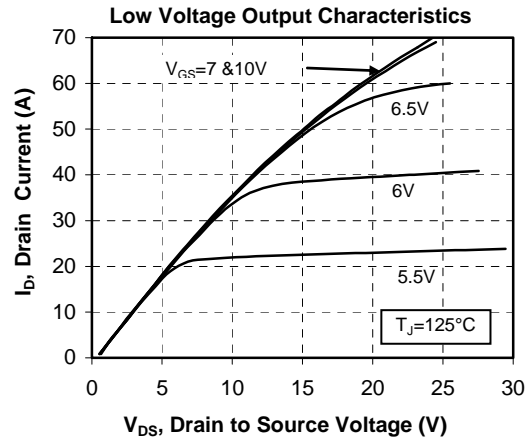
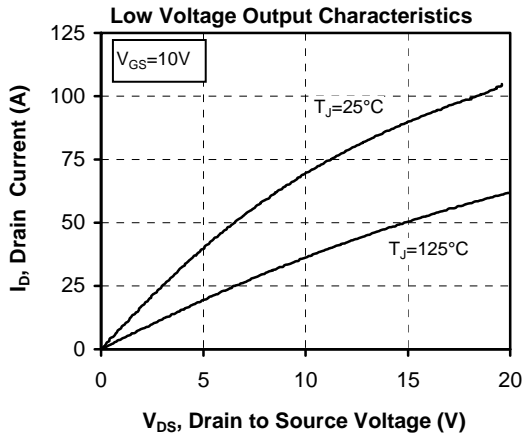
Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit	
$I_S$	Continuous Source current (Body diode)		$T_c = 25^\circ\text{C}$			25	A
			$T_c = 80^\circ\text{C}$			19	
$V_{SD}$	Diode Forward Voltage	$V_{GS} = 0\text{V}, I_S = -21\text{A}$			1	V	
$dv/dt$	Peak Diode Recovery ❶				30	V/ns	
$t_{rr}$	Reverse Recovery Time	$I_S = -21\text{A}$ $V_R = 100\text{V}$ $di_s/dt = 100\text{A}/\mu\text{s}$	$T_j = 25^\circ\text{C}$			215	ns
			$T_j = 125^\circ\text{C}$			370	
$Q_{rr}$	Reverse Recovery Charge		$T_j = 25^\circ\text{C}$		0.90		$\mu\text{C}$
			$T_j = 125^\circ\text{C}$		2.6		

 ❶  $dv/dt$  numbers reflect the limitations of the circuit rather than the device itself.

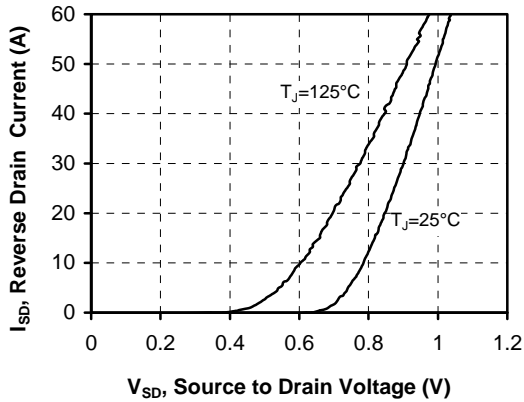
 $I_S \leq -21\text{A}$     $di/dt \leq 1000\text{A}/\mu\text{s}$     $V_{DD} \leq 333\text{V}$     $T_j \leq 125^\circ\text{C}$



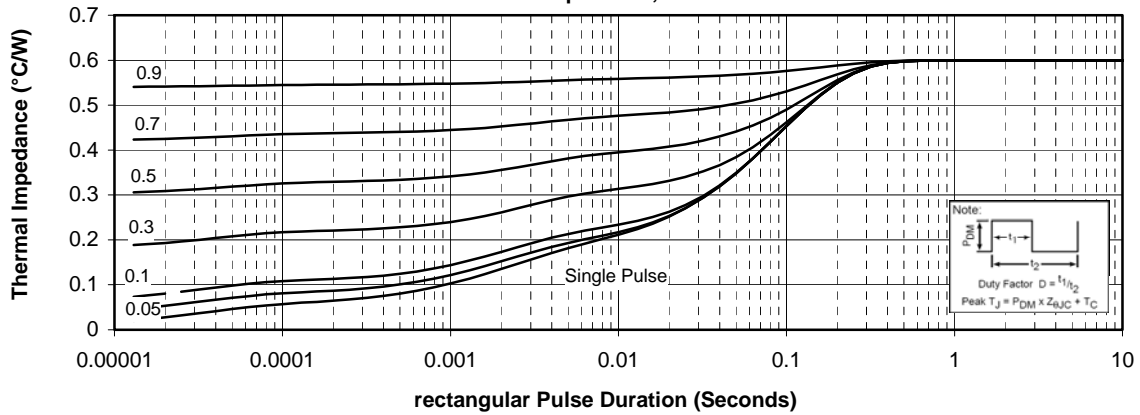
## Typical Performance Curve



Drain Current vs Source to Drain Voltage



Maximum Effective Transient Thermal Impedance, Junction to Case vs Pulse Duration



Microsemi reserves the right to change, without notice, the specifications and information contained herein

Microsemi's products are covered by one or more of U.S. patents 4,895,810 5,045,903 5,089,434 5,182,234 5,019,522 5,262,336 6,503,786 5,256,583 4,748,103 5,283,202 5,231,474 5,434,095 5,528,058 and foreign patents. U.S. and Foreign patents pending. All Rights Reserved.